Smart Highside Power Switch

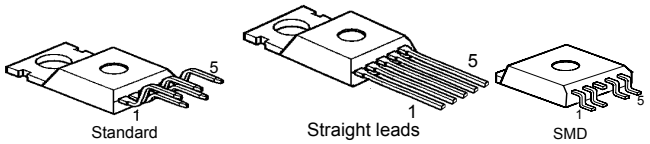
Product Summary

Overvoltage protection	$V_{bb(AZ)}$	65	V
Operating voltage	$V_{bb(on)}$	5.8 ... 58	V
On-state resistance	R_{ON}	250	mΩ
Load current (ISO)	$I_{L(ISO)}$	1.7	A

Features

- Overload protection
- Current limitation
- Short circuit protection
- Thermal shutdown
- Overvoltage protection
- Fast demagnetization of inductive loads
- Reverse battery protection[1)]
- Open drain diagnostic output
- Open load detection in OFF-state
- CMOS compatible input
- Loss of ground and loss of V_{bb} protection
- **E**lectro**s**tatic **d**ischarge (**ESD**) protection

TO-220AB/5

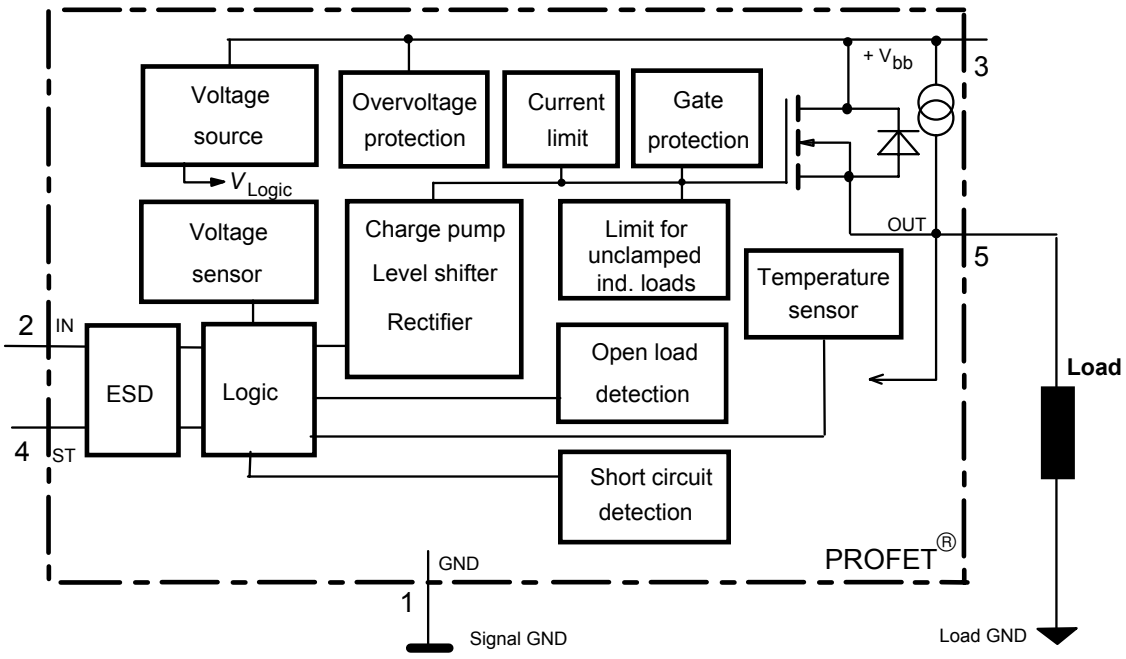


Application

- ∝C compatible power switch with diagnostic feedback for 12 V and 24 V DC grounded loads
- Most suitable for inductive loads
- Replaces electromechanical relays, fuses and discrete circuits

General Description

N channel vertical power FET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS® technology. Providing embedded protective functions.



[1)] With external current limit (e.g. resistor R_{GND}=150 Ω) in GND connection, resistor in series with ST connection, reverse load current limited by connected load.

Pin	Symbol		Function
1	GND	-	Logic ground
2	IN	I	Input, activates the power switch in case of logical high signal
3	Vbb	+	Positive power supply voltage, the tab is shorted to this pin
4	ST	S	Diagnostic feedback
5	OUT (Load, L)	O	Output to the load

Maximum Ratings at T_j = 25 °C unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 3)	V_{bb}	65	V
Supply voltage for full short circuit protection[2)] $T_{j\,Start}$=-40 ...+150°C	V_{bb}	40	V
Load current (Short circuit current, see page 4)	I_L	self-limited	A
Operating temperature range Storage temperature range	T_j T_{stg}	-40 ...+150 -55 ...+150	°C
Power dissipation (DC), $T_C \leq 25$ °C	P_{tot}	50	W
Electrostatic discharge capability (ESD) IN, ST: (Human Body Model) all other pins:	V_{ESD}	1.0 tbd (>1.0)	kV
Input voltage (DC)	V_{IN}	-0.5 ... +36	V
Current through input pin (DC) Current through status pin (DC) see internal circuit diagrams page 5	I_{IN} I_{ST}	±2.0 ±5.0	mA

Thermal Characteristics

Parameter and Conditions		Symbol	Values			Unit
			min	typ	max	
Thermal resistance	chip - case:	R_{thJC}	--	--	2.5	K/W
	junction - ambient (free air):	R_{thJA}	--	--	75	

2) Status fault signal in case of short to GND. Internal thermal shutdown after several milliseconds. External shutdown in response to the status fault signal in less than about 1 ms necessary, if the device is used with higher V_{bb}.

Electrical Characteristics

Parameter and Conditions at T_j = 25 °C, V_{bb} = 12 V unless otherwise specified	Symbol	Values			Unit
		min	typ	max	
Load Switching Capabilities and Characteristics					
On-state resistance (pin 3 to 5) I_L = 2 A, V_{bb} = 24 V T_j=25 °C: T_j=150 °C:	R_{ON}	--	220 390	250 500	mΩ
Nominal load current, ISO Norm (pin 3 to 5) V_{ON} = 0.5 V, T_C = 85 °C	$I_{L(ISO)}$	1.4	1.7	--	A
Output current (pin 5) while GND disconnected or GND pulled up, V_{bb}=32 V, V_{IN}= 0, see diagram page 6	$I_{L(GNDhigh)}$	--	--	1.1	mA
Turn-on time to 90% V_{OUT}: Turn-off time to 10% V_{OUT}: R_L = 12 Ω, V_{bb} = 20V, T_j =-40...+150°C	t_{on} t_{off}	15 20	-- --	80 70	∝s
Slew rate on, 10 to 30% V_{OUT}, R_L = 12 Ω, V_{bb} = 20V, T_j =-40...+150°C	dV/dt_{on}	--	--	6	V/∝s
Slew rate off, 10 to 30% V_{OUT}, R_L = 12 Ω, V_{bb} = 20V, T_j =-40...+150°C	$-dV/dt_{off}$	--	--	7	V/∝s
Operating Parameters					
Operating voltage [3] T_j =-40...+150°C:	$V_{bb(on)}$	5.8	--	58	V
Undervoltage shutdown T_j =-40...+150°C:	$V_{bb(under)}$	2.7	--	4.7	V
Undervoltage restart T_j =-40...+150°C:	$V_{bb(u\ rst)}$	--	--	4.9	V
Undervoltage restart of charge pump see diagram page 10 T_j =-40...+150°C:	$V_{bb(ucp)}$	--	5.6	7.5	V
Undervoltage hysteresis $\Delta V_{bb(under)} = V_{bb(u\ rst)} - V_{bb(under)}$	$\Delta V_{bb(under)}$	--	0.4	--	V
Overvoltage protection[4] T_j =-40...+150°C: I_{bb}=40 mA	$V_{bb(AZ)}$	65	70	--	V
Standby current (pin 3), V_{IN}=0 T_j=-40...+150°C:	$I_{bb(off)}$	--	10	50	∝A
Operating current (Pin 1)[5], V_{IN}=5 V	I_{GND}	--	2.2	--	mA

[3] At supply voltage increase up to V_{bb}= 5.6 V typ without charge pump, $V_{OUT} \approx V_{bb}$ - 2 V
[4] See also $V_{ON(CL)}$ in table of protection functions and circuit diagram page 6.
[5] Add I_{ST}, if I_{ST} > 0, add I_{IN}, if V_{IN}>5.5 V

Parameter and Conditions at T_j = 25 °C, V_{bb} = 12 V unless otherwise specified	Symbol	Values			Unit
		min	typ	max	
Protection Functions[6]					
Initial peak short circuit current limit (pin 3 to 5)	$I_{L(SCp)}$				
T_j =-40°C:		--	--	19	A
T_j =25°C:		--	10	--	
T_j =+150°C:		4.0	--	--	
Output clamp (inductive load switch off) at $V_{OUT} = V_{bb} - V_{ON(CL)}$ I_L= 1 A, T_j =-40..+150°C:	$V_{ON(CL)}$	59	--	75	V
Thermal overload trip temperature	T_{jt}	150	--	--	°C
Thermal hysteresis	ΔT_{jt}	--	10	--	K
Reverse battery (pin 3 to 1) [7]	$-V_{bb}$	--	--	32	V
Diagnostic Characteristics					
Open load detection current (included in standby current $I_{bb(off)}$)	$I_{L(off)}$	--	6	--	∝A
Open load detection voltage T_j=-40..150°C:	$V_{OUT(OL)}$	2.4	3	4	V
Short circuit detection voltage (pin 3 to 5)	$V_{ON(SC)}$	--	2.5	--	V
Input and Status Feedback[8]					
Input resistance see circuit page 5	R_I	--	20	--	kΩ
Input turn-on threshold voltage	$V_{IN(T+)}$	1	--	2.5	V
Input turn-off threshold voltage	$V_{IN(T-)}$	0.8	--	--	V
Input threshold hysteresis	$\Delta V_{IN(T)}$	--	0.5	--	V
Off state input current (pin 2), V_{IN} = 0.4 V	$I_{IN(off)}$	1	--	30	∝A
On state input current (pin 2), V_{IN} = 3.5? V	$I_{IN(on)}$	10	25	70	∝A
Delay time for status with open load after Input neg. slope (see diagram page 10)	$t_{d(ST\ OL3)}$	--	200	--	∝s
Status output (open drain)					
Zener limit voltage T_j =-40...+150°C, I_{ST} = +1.6 mA:	$V_{ST(high)}$	5.4	6.1	--	V
ST low voltage T_j =-40...+150°C, I_{ST} = +1.6 mA:	$V_{ST(low)}$	--	--	0.4	

[6] Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

[7] Requires 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Note that the power dissipation is higher compared to normal operating conditions due to the voltage drop across the intrinsic drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 2 and circuit page 6).

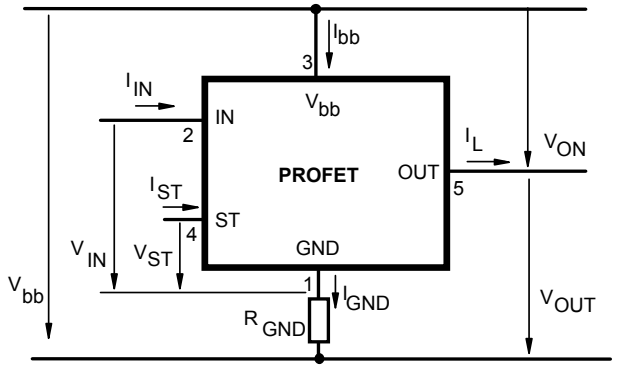
[8] If a ground resistor R_{GND} is used, add the voltage drop across this resistor.

Truth Table

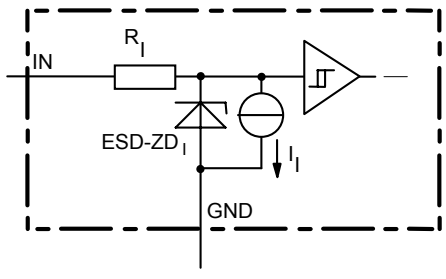
	Input-	Output	Status
	level	level	BTS 307 BTS 707
Normal operation	L H	L H	L H
Open load	L H	[9]) H	H H
Short circuit to GND	L H	L L	L L
Short circuit to V_{bb}	L H	H H	H H
Overtem-perature	L H	L L	L L
Under-voltage	L H	L L	L L
Overvoltage	no overvoltage shutdown, see normal operation		

L = "Low" Level X = don't care Z = high impedance, potential depends on external circuit
H = "High" Level Status signal after the time delay shown in the diagrams (see fig 5. page 10)

Terms

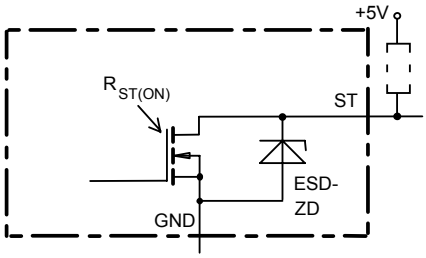


Input circuit (ESD protection)



ESD zener diodes are not to be used as voltage clamp at DC conditions. Operation in this mode may result in a drift of the zener voltage (increase of up to 1 V).

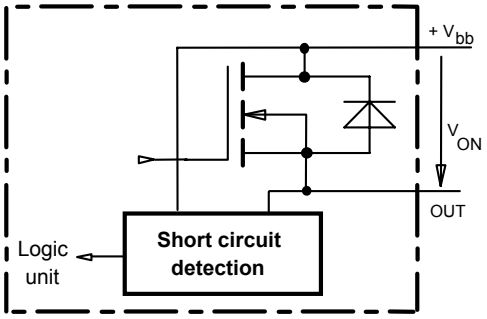
Status output



ESD-Zener diode: 6.1 V typ., max 5 mA;
$R_{ST(ON)}$ < 0 Ω at 1.6 mA, ESD zener diodes are not to be used as voltage clamp at DC conditions. Operation in this mode may result in a drift of the zener voltage (increase of up to 1 V).

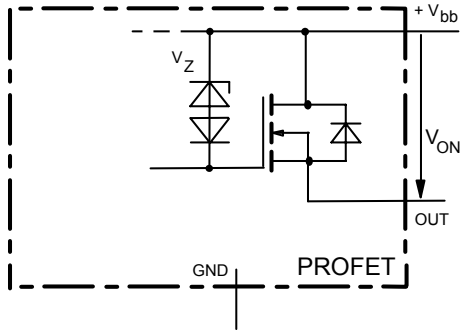
Short circuit detection

Fault Signal at ST-Pin: V_{ON} > 2.5 V typ, no switch off by the PROFET itself, external switch off recommended!



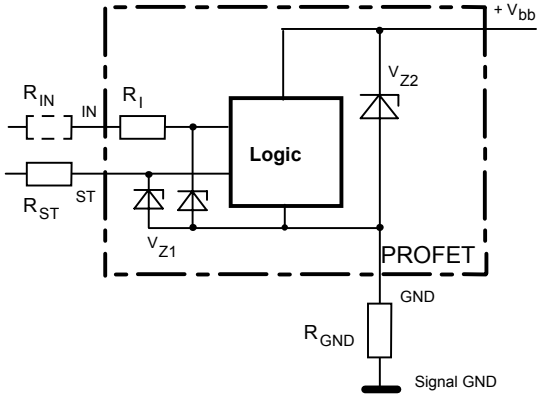
[9]) Power Transistor off, high impedance, internal pull up current source for open load detection.

Inductive and overvoltage output clamp



V_{ON} clamped to -- V typ.

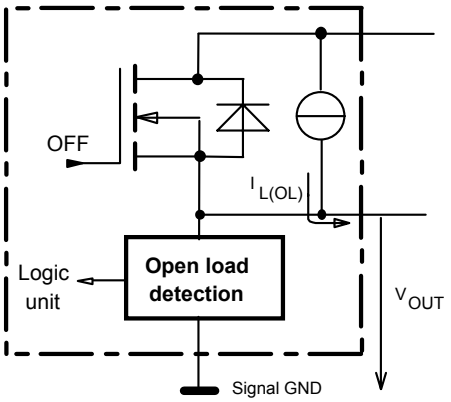
Overvolt. and reverse batt. protection



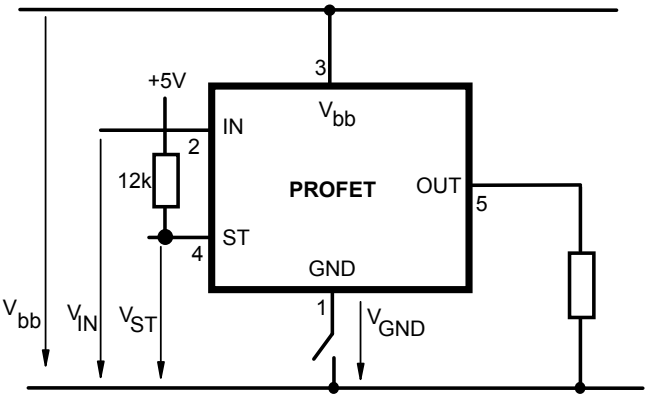
V_{Z1} = 6.2 V typ., V_{Z2} = 70 V typ., R_{GND} = 150 Ω, R_{ST}= 15 kΩ, R_I= 20 kΩ typ.

Open-load detection

OFF-state diagnostic condition: V_{OUT} > 3 V typ.; IN low

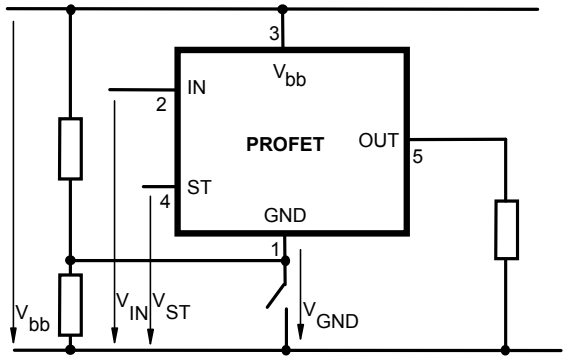


GND disconnect



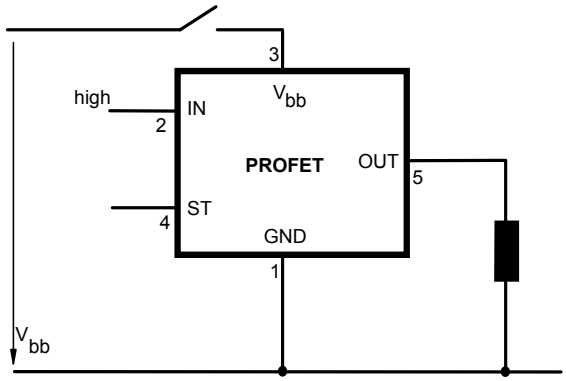
For V_{bb}=24V and V_{IN}=0V: V_{ST}>2.8V @ $I_{ST} \geq 0$ if pulled up as shown. Any kind of load. In case of Input=high is $V_{OUT} \approx V_{IN} - V_{IN(T+)}$.

GND disconnect with GND pull up



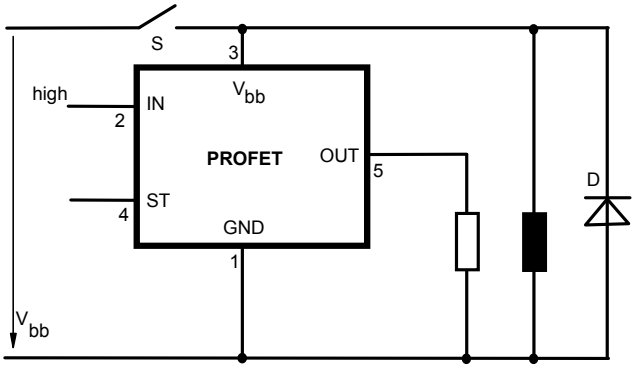
Any kind of load. If $V_{GND} > V_{IN} - V_{IN(T+)}$ device stays off
Due to V_{GND} >0, no V_{ST} = low signal available.

V_{bb} disconnect with energized inductive load



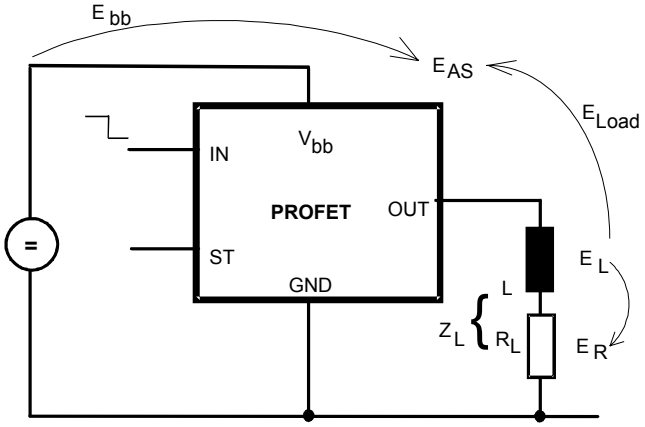
Normal load current can be handled by the PROFET itself.

V_{bb} disconnect with charged external inductive load



If other external inductive loads L are connected to the PROFET, additional elements like D are necessary.

Inductive Load switch-off energy dissipation



Energy stored in load inductance:

$$E_L = {}^1/_2 \cdot L \cdot I_L^2$$

While demagnetizing load inductance, the energy dissipated in PROFET is

$$E_{AS} = E_{bb} + E_L - E_R = \int V_{ON(CL)} \cdot i_L(t)\, dt,$$

with an approximate solution for $R_L > 0\,\Omega$:

$$E_{AS} = \frac{I_L \cdot L}{2 \cdot R_L} \cdot (V_{bb} + |V_{OUT(CL)}|) \cdot ln\left(1 + \frac{I_L \cdot R_L}{|V_{OUT(CL)}|}\right)$$

Options Overview

all versions: High-side switch, Input protection, ESD protectionand reverse battery protection with 150 Ω in GND connection, protection against loss of ground

Type BTS	410D2	410E2	410G2	410H2	**307**	308
Logic version	D	E	G	H		
Overtemperature protection with hysteresis						
T_j >150 °C, latch function[10)][11)]	X			X		X
T_j >150 °C, with auto-restart on cooling		X	X		**X**	
Short circuit to GND protection						
switches off when V_{ON}>3.5 V typ. and V_{bb}> 8 V typ[10)] (when first turned on after approx. 150 ∝s)				X		X
switches off when V_{ON}>8.5 V typ.[10)] (when first turned on after approx. 150 ∝s)	X	X				
Achieved through overtemperature protection			X		**X**	
Open load detection						
in OFF-state with sensing current 6 ∝A typ.				X	**X**	X
in ON-state with sensing voltage drop across power transistor	X	X	X			
Undervoltage shutdown with auto restart	X	X	X	X	**X**	X
Overvoltage shutdown with auto restart	X	X	X	X	**-**	X
Status feedback for						
overtemperature	X	X	X	X	**X**	X
short circuit to GND	X	X	-	X	**X**	X
short to V_{bb}	-[12)]	-[**12**)]	-[12)]	X	**X**	X
open load	X	X	X	X	**X**	X
undervoltage	X	-	-	-	**X**	-
overvoltage	X	-	-	-	**-**	-
Status output type						
CMOS	X					
Open drain		X	X	X	**X**	X
Output negative voltage transient limit (fast inductive load switch off)						
to V_{bb} - $V_{ON(CL)}$	X	X	X	X	**X**	X
Load current limit						
high level (can handle loads with high inrush currents)	X	X				
low level (better protection of application)			X	X	**X**	X
Protection against loss of GND	X	X	X	X	**X**	X

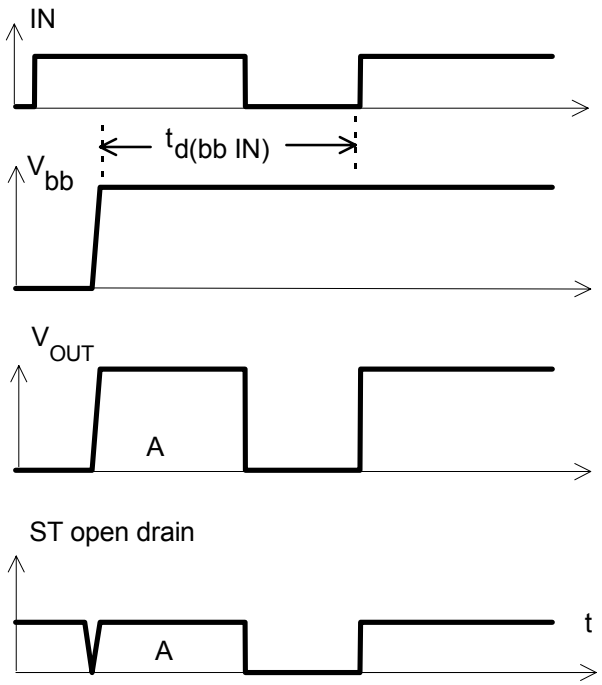
[10)] Latch except when V_{bb} -V_{OUT} < $V_{ON(SC)}$ after shutdown. In most cases V_{OUT} = 0 V after shutdown (V_{OUT} ≠ 0 V only if forced externally). So the device remains latched unless V_{bb} < $V_{ON(SC)}$ (see page 4). No latch between turn on and $t_{d(SC)}$.

[11)] With latch function. Reseted by a) Input low, b) Undervoltage, c) Overvoltage

[12)] Low resistance short V_{bb} to output may be detected in ON-state by the no-load-detection

Timing diagrams

Figure 1a: V_{bb} turn on, :



in case of too early V_{IN}=high the device may not turn on (curve A)
$t_{d(bb\ IN)}$ approx. 150 ∝s

Figure 2a: Switching an inductive load,

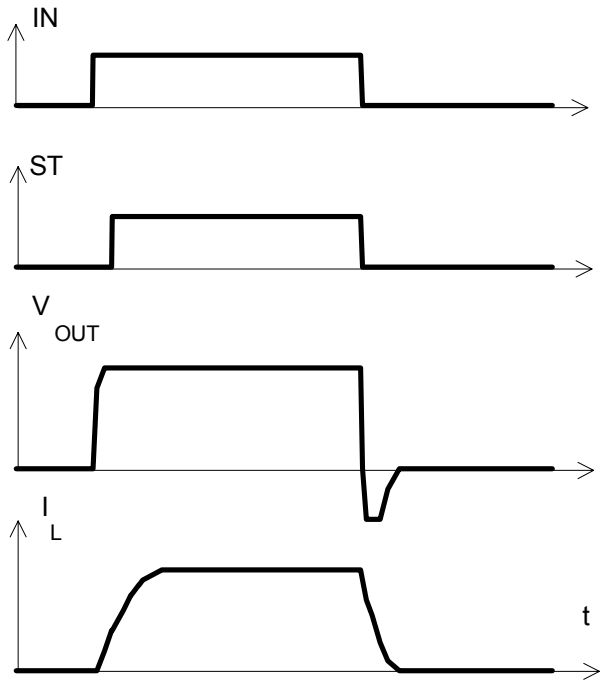
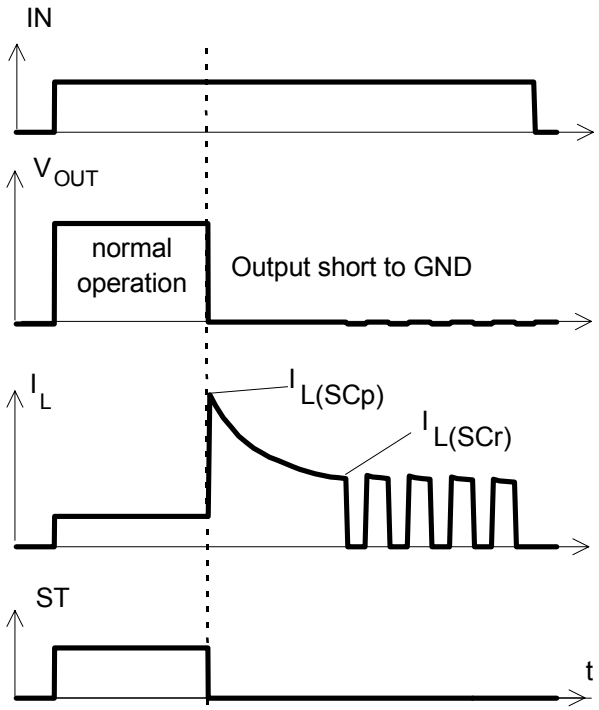


Figure 3a: Short circuit:
shut down by overtempertature, reset by cooling



Heating up requires several milliseconds, depending on external conditions. External shutdown in response to status fault signal recommended.

Figure 4a: Overtemperature:
Reset if $T_j < T_{jt}$

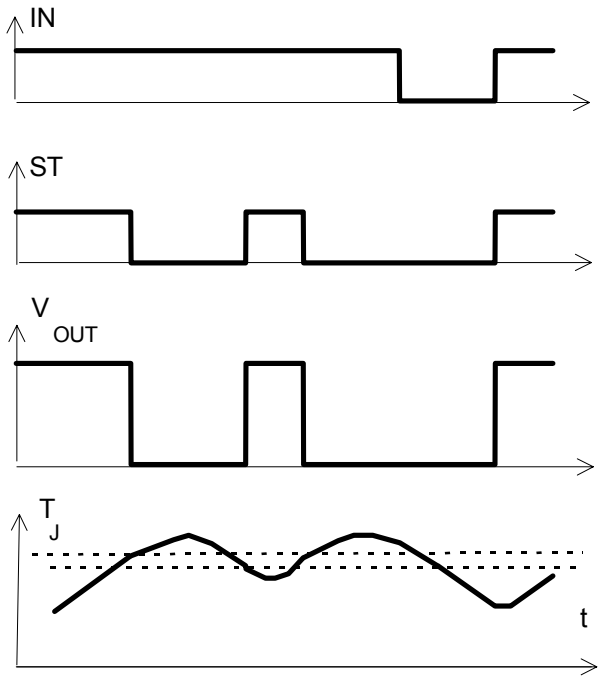
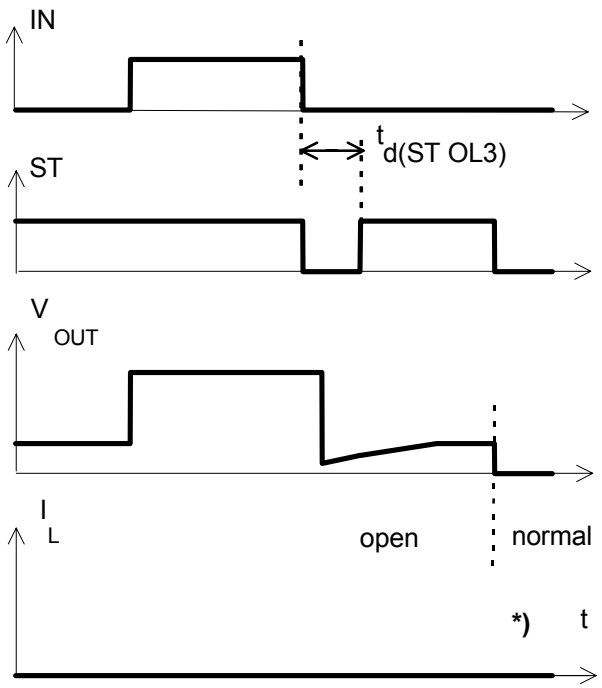


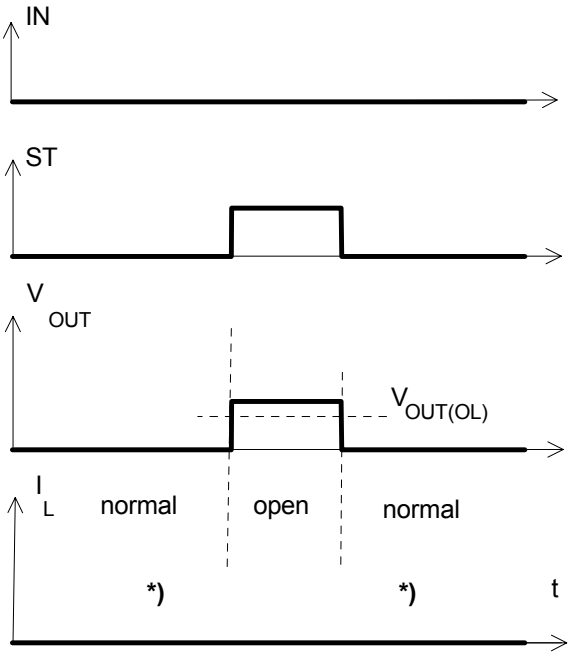
Figure 5a: Open load, : detection in OFF-state, turn on/off to open load



$t_{d(ST,OL3)}$ depends on external circuitry because of high impedance

*) I_L = 6 ∝A typ

Figure 5b: Open load, : detection in OFF-state, open load occurs in off-state



*) I_L = 6 ∝A typ

Figure 6a: Undervoltage:

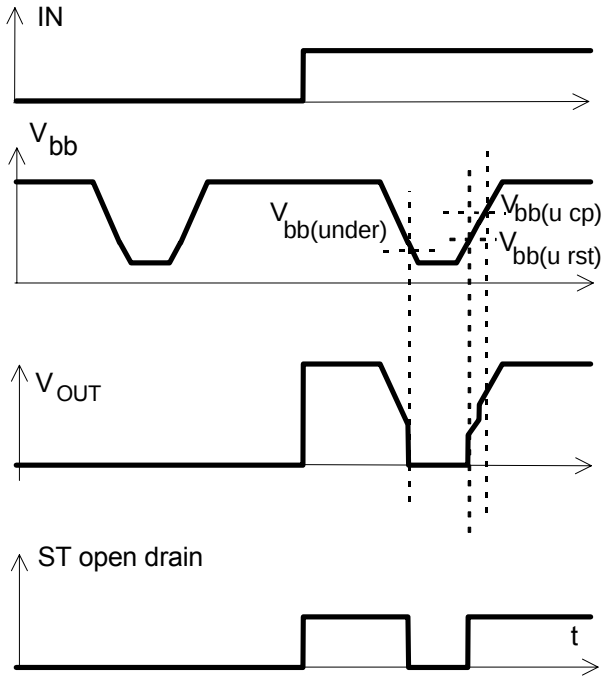
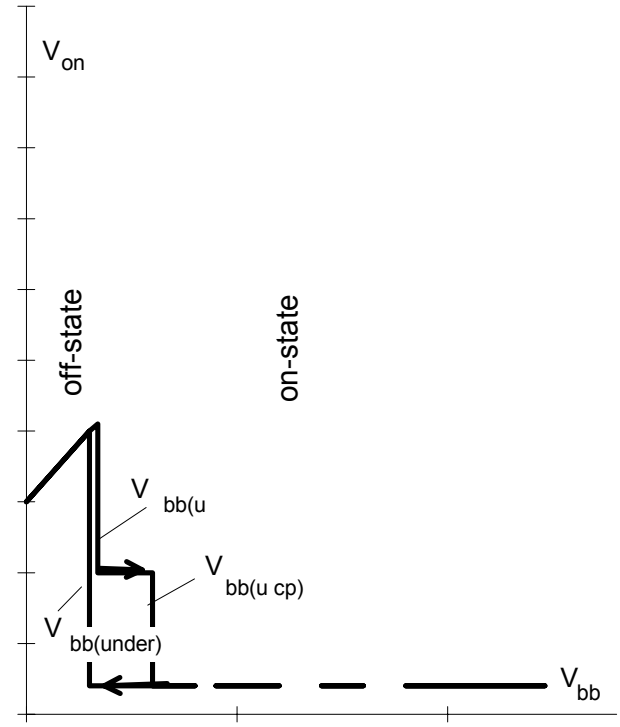
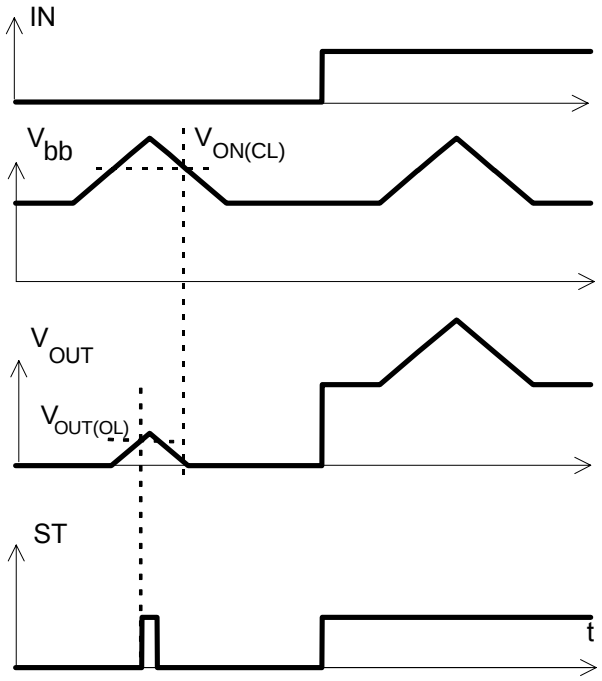


Figure 6b: Undervoltage restart of charge pump



charge pump starts at $V_{bb(ucp)}$ =5.6 V typ.

Figure 7a: Overvoltage, no shutdown:

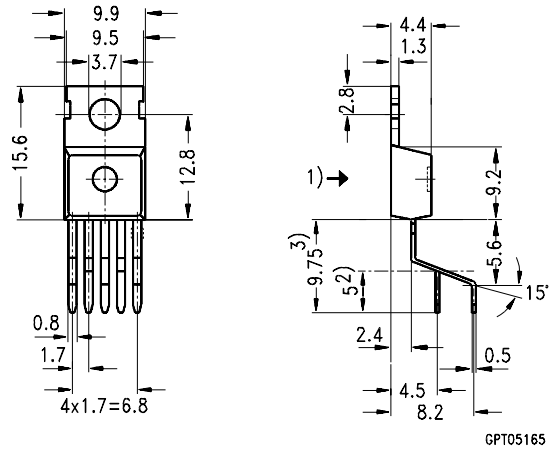


Package and Ordering Code

All dimensions in mm

Standard TO-220AB/5 Ordering code

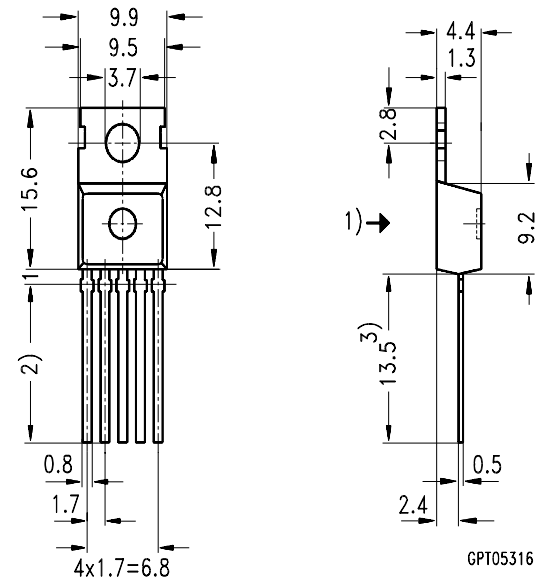
BTS 307		tbd



1) shear and punch direction no burrs this surface
2) min. length by tinning
3) max. 11 mm allowable by tinning

TO-220AB/5, Option E3043 Ordering code

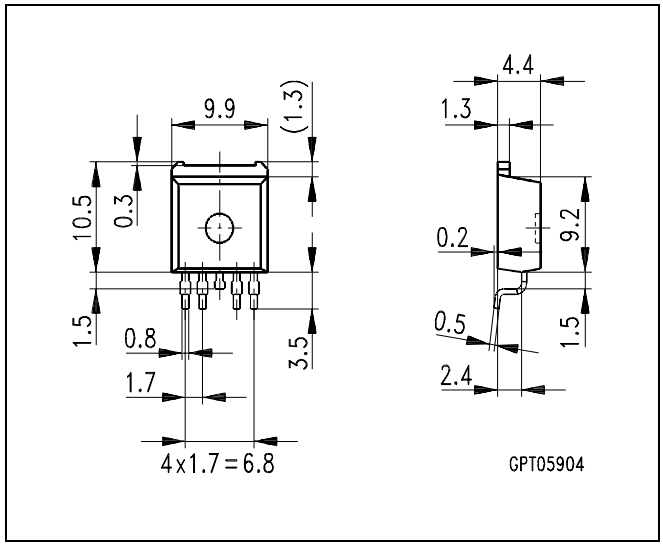
BTS 307 E3043		C67078-S5204-A3



1) punch direction, burr max. 0.04
2) dip tinning
3) max. 14.5 by dip tinning press burr max. 0.05

SMD TO-220AB/5, Opt. E3062 Ordering code

BTS 307 E3062A	T&R:	C67078-S5204-A4



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For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives worldwide (see address list).

Warnings
Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.